Abstracts

200-GHz 50-mW CW Oscillation with Silicon SDR IMPATT (Short Papers)

T. Ishibashi and M. Ohmori. "200-GHz 50-mW CW Oscillation with Silicon SDR IMPATT (Short Papers)." 1976 Transactions on Microwave Theory and Techniques 24.11 (Nov. 1976 [T-MTT] (Special Issue on Millimeter Waves: Circuits, Components, and Systems)): 858-859.

Silicoin SDR IMPATT diodes have been operated continuously in 200- and 300-GHz bands. A p+-n junction structure was formed by thermal diffusion of boron and ion implantation of phosphorus ions. CW output power of 50 mW was obtained at 202 GHz with 1.3-percent conversion efficiency. At 301-GHz CW output power of 1.2 MW was observed.

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